

Anne Henry

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

141
papers

1,139
citations

18
h-index

25
g-index

142
ext. papers

1,228
ext. citations

1.5
avg, IF

3.77
L-index

#	Paper	IF	Citations
141	Chloride-based CVD growth of silicon carbide for electronic applications. <i>Chemical Reviews</i> , 2012 , 112, 2434-53	68.1	80
140	Growth of High Quality Epitaxial Rhombohedral Boron Nitride. <i>Crystal Growth and Design</i> , 2012 , 12, 3215-3220	5.3	54
139	Epitaxial CVD growth of sp ² -hybridized boron nitride using aluminum nitride as buffer layer. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011 , 5, 397-399	2.5	38
138	Growth characteristics of chloride-based SiC epitaxial growth. <i>Physica Status Solidi - Rapid Research Letters</i> , 2008 , 2, 278-280	2.5	29
137	Electron paramagnetic resonance and theoretical studies of shallow phosphorous centers in 3C-, 4H-, and 6H-SiC. <i>Physical Review B</i> , 2006 , 73,	3.3	29
136	Micropipe Healing in Liquid Phase Epitaxial Growth of SiC. <i>Materials Science Forum</i> , 2000 , 338-342, 237-240	1.4	28
135	Material characterization need for SiC-based devices. <i>Materials Science in Semiconductor Processing</i> , 2001 , 4, 181-186	4.3	27
134	Fast SiC Epitaxial Growth in a Chimney CVD Reactor and HTCVD Crystal Growth Developments. <i>Materials Science Forum</i> , 2000 , 338-342, 131-136	0.4	27
133	Phonon replicas at the M point in 4H-SiC: A theoretical and experimental study. <i>Physical Review B</i> , 1998 , 58, 13634-13647	3.3	26
132	Polytype Pure sp ² -BN Thin Films As Dictated by the Substrate Crystal Structure. <i>Chemistry of Materials</i> , 2015 , 27, 1640-1645	9.6	24
131	Very high crystalline quality of thick 4H-SiC epilayers grown from methyltrichlorosilane (MTS). <i>Physica Status Solidi - Rapid Research Letters</i> , 2008 , 2, 188-190	2.5	23
130	Review Article: Challenge in determining the crystal structure of epitaxial 0001 oriented sp ² -BN films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018 , 36, 030801	2.9	22
129	On the effect of silicon in CVD of sp ² hybridized boron nitride thin films. <i>CrystEngComm</i> , 2013 , 15, 455-458	3.8	21
128	High Growth Rate of 4H-SiC Epilayers on On-Axis Substrates with Different Chlorinated Precursors. <i>Crystal Growth and Design</i> , 2010 , 10, 5334-5340	3.5	20
127	Chloride-based CVD of 3C-SiC epitaxial layers on 6H(0001) SiC. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010 , 4, 305-307	2.5	20
126	Investigations of Possible Nitrogen Participation in the Z1/Z2 Defect in 4H-SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 469-472	0.4	20
125	Influence of Epitaxial Growth and Substrate Induced Defects on the Breakdown of High-voltage 4H-SiC Schottky Diodes. <i>Materials Science Forum</i> , 2000 , 338-342, 1175-1178	0.4	20

124	Low Temperature CVD of Thin, Amorphous Boron-Carbon Films for Neutron Detectors. <i>Chemical Vapor Deposition</i> , 2012 , 18, 221-224		19
123	Homoepitaxial Growth of 4H-SiC on On-Axis Si-Face Substrates Using Chloride-Based CVD. <i>Materials Science Forum</i> , 2008 , 600-603, 107-110	0.4	17
122	Photoluminescence of the two-dimensional hole gas in p-type delta -doped Si layers. <i>Physical Review B</i> , 1996 , 53, 9587-9590	3.3	17
121	A SiC Varactor With Large Effective Tuning Range for Microwave Power Applications. <i>IEEE Electron Device Letters</i> , 2011 , 32, 788-790	4.4	16
120	CVD Growth and Characterisation of SiC Epitaxial Layers on Faces Perpendicular to the (0001) Basal Plane. <i>Materials Science Forum</i> , 1998 , 264-268, 123-126	0.4	16
119	Initial stages of growth and the influence of temperature during chemical vapor deposition of sp ² -BN films. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2015 , 33, 061520	2.9	15
118	Double-Position-Boundaries Free 3C-SiC Epitaxial Layers Grown on On-Axis 4H-SiC. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, P75-P81	2	15
117	Gas-Phase Modeling of Chlorine-Based Chemical Vapor Deposition of Silicon Carbide. <i>Crystal Growth and Design</i> , 2012 , 12, 1977-1984	3.5	15
116	Characterization of Bulk and Epitaxial SiC Material Using Photoluminescence Spectroscopy. <i>Materials Science Forum</i> , 2002 , 389-393, 593-596	0.4	15
115	Growth and Characterisation of SiC Power Device Material. <i>Materials Science Forum</i> , 1998 , 264-268, 97-102	4	15
114	Comparative Studies of Carrier Dynamics in 3C-SiC Layers Grown on Si and 4H-SiC Substrates. <i>Journal of Electronic Materials</i> , 2011 , 40, 394-399	1.9	14
113	High Voltage (>2.5kV) 4H-SiC Schottky Rectifiers Processed on Hot-Wall CVD and High-Temperature CVD Layers. <i>Materials Science Forum</i> , 1998 , 264-268, 921-924	0.4	13
112	Electrical Characterization of the Gallium Acceptor in 4H- and 6H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 557-560	0.4	13
111	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1462-1466	2.8	12
110	SiC epitaxy growth using chloride-based CVD. <i>Physica B: Condensed Matter</i> , 2012 , 407, 1467-1471	2.8	12
109	SiC Varactors for Dynamic Load Modulation of High Power Amplifiers. <i>IEEE Electron Device Letters</i> , 2008 , 29, 728-730	4.4	12
108	Epitaxial Growth and Characterisation of Phosphorus Doped SiC Using TBP as Precursor. <i>Materials Science Forum</i> , 2005 , 483-485, 101-104	0.4	12
107	Growth and Characterisation of Thick SiC Epilayers by High Temperature CVD. <i>Materials Science Forum</i> , 1998 , 264-268, 103-106	0.4	12

106	Chloride-Based SiC Epitaxial Growth toward Low Temperature Bulk Growth. <i>Crystal Growth and Design</i> , 2010 , 10, 3743-3751	3.5	11
105	Electrothermal actuation of silicon carbide ring resonators. <i>Journal of Vacuum Science & Technology B</i> , 2009 , 27, 3109		11
104	Growth and Properties of SiC On-Axis Homoepitaxial Layers. <i>Materials Science Forum</i> , 2010 , 645-648, 83-88	0.4	9
103	Carrier Removal in Electron Irradiated 4H and 6H SiC. <i>Materials Science Forum</i> , 2008 , 600-603, 425-428	0.4	9
102	On the effect of water and oxygen in chemical vapor deposition of boron nitride. <i>Thin Solid Films</i> , 2012 , 520, 5889-5893	2.2	8
101	Fabrication of beam resonators from hot-wall chemical vapour deposited SiC. <i>Microelectronic Engineering</i> , 2009 , 86, 1194-1196	2.5	8
100	Investigation of an Ion-Implantation Induced High Temperature Persistent Intrinsic Defect in SiC. <i>Materials Science Forum</i> , 2001 , 353-356, 377-380	0.4	8
99	High Growth Rate Epitaxy of Thick 4H-SiC Layers. <i>Materials Science Forum</i> , 2000 , 338-342, 165-168	0.4	8
98	Effect of ion bombardment on deep photoluminescence bands in p-type boron-modulation-doped Si layers grown by molecular-beam epitaxy. <i>Physical Review B</i> , 1995 , 52, 12006-12012	3.3	8
97	Electrical Characterization of PiN Diodes with p+ Layer Selectively Grown by VLS Transport. <i>Materials Science Forum</i> , 2013 , 740-742, 911-914	0.4	7
96	Chloride-Based CVD at High Rates of 4H-SiC on On-Axis Si-Face Substrates. <i>Materials Science Forum</i> , 2011 , 679-680, 59-62	0.4	7
95	Chloride-Based CVD at High Growth Rates on 3° Vicinal Off-Angles SiC Wafers. <i>Materials Science Forum</i> , 2010 , 645-648, 107-110	0.4	7
94	Growth of Thick 4H-SiC Epitaxial Layers on On-Axis Si-Face Substrates with HCl Addition. <i>Materials Science Forum</i> , 2009 , 615-617, 93-96	0.4	7
93	Bistable defects in low-energy electron irradiated n-type 4H-SiC. <i>Physica Status Solidi - Rapid Research Letters</i> , 2010 , 4, 227-229	2.5	7
92	SiC and III-Nitride Growth in Hot-Wall CVD Reactor. <i>Materials Science Forum</i> , 2005 , 483-485, 61-66	0.4	7
91	Excitation properties of hydrogen-related photoluminescence in 6H-SiC. <i>Physical Review B</i> , 2000 , 62, 7162-7168	3.3	7
90	Metastability of a Hydrogen-related Defect in 6H-SiC. <i>Materials Science Forum</i> , 2000 , 338-342, 651-654	0.4	7
89	Thickness Contour Mapping of SiC Epi-Films on SiC Substrates. <i>Materials Science Forum</i> , 1998 , 264-268, 645-648	0.4	7

88	3C-SiC Heteroepitaxy on Hexagonal SiC Substrates. <i>Materials Science Forum</i> , 2013 , 740-742, 257-262	0.4	6
87	Surface Preparation of 4° Off-Axis 4H-SiC Substrate for Epitaxial Growth. <i>Materials Science Forum</i> , 2013 , 740-742, 225-228	0.4	6
86	Defects in 4H-SiC Layers Grown by Chloride-Based Epitaxy. <i>Materials Science Forum</i> , 2009 , 615-617, 373-376	0.4	6
85	Chloride Based CVD of 3C-SiC on (0001) SiC Substrates. <i>Materials Science Forum</i> , 2011 , 679-680, 75-78	0.4	6
84	Carrot Defect Control in Chloride-Based CVD through Optimized Ramp up Conditions. <i>Materials Science Forum</i> , 2012 , 717-720, 109-112	0.4	6
83	4H-SiC Epitaxial Layers Grown on On-Axis Si-Face Substrate. <i>Materials Science Forum</i> , 2007 , 556-557, 53-56	0.4	6
82	Growth of High Quality p-Type 4H-SiC Substrates by HTCVD. <i>Materials Science Forum</i> , 2003 , 433-436, 21-24	0.4	6
81	Stacking Fault Formation in Highly Doped 4H-SiC Epilayers during Annealing. <i>Materials Science Forum</i> , 2003 , 433-436, 253-256	0.4	6
80	Presence of Hydrogen in SiC. <i>Materials Science Forum</i> , 2001 , 353-356, 373-376	0.4	6
79	Designing, Physical Simulation and Fabrication of High-Voltage (3.85 kV) 4H-SiC Schottky Rectifiers Processed on Hot-Wall and Chimney CVD Films. <i>Materials Science Forum</i> , 2000 , 338-342, 1171-1174	0.4	6
78	Cathodoluminescence of Defect Regions in SiC Epi-Films. <i>Materials Science Forum</i> , 1998 , 264-268, 653-656	0.4	6
77	S-Cu-related metastable complex defect in Si by optical detection of magnetic resonance. <i>Physical Review B</i> , 1994 , 50, 7365-7370	3.3	6
76	Early stages of growth and crystal structure evolution of boron nitride thin films. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FD06	1.4	6
75	Comparison of Bottom-Up and Top-Down 3C-SiC NWFETs. <i>Materials Science Forum</i> , 2016 , 858, 1001-1005	0.4	5
74	High Growth Rate with Reduced Surface Roughness during On-Axis Homoepitaxial Growth of 4H-SiC. <i>Materials Science Forum</i> , 2011 , 679-680, 115-118	0.4	5
73	6H-Type Zigzag Faults in Low-Doped 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2010 , 645-648, 347-350	0.4	5
72	Single Crystal and Polycrystalline 3C-SiC for MEMS Applications. <i>Materials Science Forum</i> , 2009 , 615-617, 625-628	0.4	5
71	Very High Growth Rate of 4H-SiC Using MTS as Chloride-Based Precursor. <i>Materials Science Forum</i> , 2008 , 600-603, 115-118	0.4	5

70	Electron Paramagnetic Resonance of Shallow Phosphorous Centers in 4H- and 6H-SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 515-518	0.4	5
69	Aluminum Doping of Epitaxial Silicon Carbide Grown by Hot-Wall CVD; Effect of Process Parameters. <i>Materials Science Forum</i> , 2002 , 389-393, 203-206	0.4	5
68	Photoluminescence Study of CVD Layers Highly Doped with Nitrogen. <i>Materials Science Forum</i> , 2000 , 338-342, 619-622	0.4	5
67	Large area mapping of the alloy composition of Al _x Ga _{1-x} N using infrared reflectivity. <i>Physica Status Solidi - Rapid Research Letters</i> , 2009 , 3, 145-147	2.5	4
66	Annealing Effects on Electrical and Optical Properties of N-ZnO/P-Si Heterojunction Diodes. <i>Advanced Materials Research</i> , 2011 , 324, 233-236	0.5	4
65	Intrinsic Defects in HPSI 6H-SiC: an EPR Study. <i>Materials Science Forum</i> , 2008 , 600-603, 381-384	0.4	4
64	Nitrogen Delta Doping in 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2003 , 433-436, 153-156	0.4	4
63	The Effect of Hydrogen Diffusion in p- and n-Type SiC Schottky Diodes at High Temperatures. <i>Materials Science Forum</i> , 2002 , 389-393, 1419-1422	0.4	4
62	Power Schottky and p-n Diodes on SiC Epi-Wafers with Reduced Micropipe Density. <i>Materials Science Forum</i> , 2002 , 389-393, 1173-1176	0.4	4
61	Pseudo-Donors in SiC. <i>Materials Science Forum</i> , 2000 , 338-342, 647-650	0.4	4
60	Applications of Vapor-Liquid-Solid Selective Epitaxy of Highly p-Type Doped 4H-SiC: PiN Diodes with Peripheral Protection and Improvement of Specific Contact Resistance of Ohmic Contacts. <i>Materials Science Forum</i> , 2014 , 778-780, 639-644	0.4	3
59	Concentrated Chloride-Based Epitaxial Growth of 4H-SiC. <i>Materials Science Forum</i> , 2010 , 645-648, 95-98	0.4	3
58	On-Axis Homoepitaxy on Full 2 μ m 4H-SiC Wafer for High Power Applications. <i>Materials Science Forum</i> , 2009 , 615-617, 133-136	0.4	3
57	Observation of Bistable Defects in Electron Irradiated N-Type 4H-SiC. <i>Materials Science Forum</i> , 2011 , 679-680, 249-252	0.4	3
56	600 V PIN Diodes Fabricated Using On-Axis 4H Silicon Carbide. <i>Materials Science Forum</i> , 2012 , 717-720, 969-972	0.4	3
55	Contact-Less Electrical Defect Characterization of Semi-Insulating 6H-SiC Bulk Material. <i>Materials Science Forum</i> , 2008 , 600-603, 405-408	0.4	3
54	A Comparison of MESFETs on Different 4H-Silicon Carbide Semi-Insulating Substrates. <i>Materials Science Forum</i> , 2003 , 433-436, 737-740	0.4	3
53	Growth Characteristics of SiC in a Hot-Wall CVD Reactor with Rotation. <i>Materials Science Forum</i> , 2002 , 389-393, 191-194	0.4	3

52	Predicting Growth Rates of SiC Epitaxial Layers Grown by Hot-Wall Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2002 , 389-393, 219-222	0.4	3
51	Some Aspects of the Photoluminescence and Raman Spectroscopy of (10-10)- and (11-20)-Oriented 4H and 6H Silicon Carbide. <i>Materials Science Forum</i> , 1998 , 264-268, 469-472	0.4	3
50	Mercury-related luminescent center in silicon. <i>Physical Review B</i> , 1993 , 47, 13309-13313	3.3	3
49	Metastable Defects in Low-Energy Electron Irradiated n-Type 4H-SiC. <i>Materials Science Forum</i> , 2010 , 645-648, 435-438	0.4	2
48	Chloride-based CVD of 3C-SiC Epitaxial Layers on On-axis 6H (0001) SiC Substrates 2010 ,		2
47	Chloride-Based SiC Epitaxial Growth. <i>Materials Science Forum</i> , 2009 , 615-617, 89-92	0.4	2
46	Chloride-Based CVD of 4H-SiC at High Growth Rates on Substrates with Different Off-Angles. <i>Materials Science Forum</i> , 2012 , 717-720, 113-116	0.4	2
45	CVD Heteroepitaxial Growth of 3C-SiC on 4H-SiC (0001) Substrates. <i>Materials Science Forum</i> , 2012 , 717-720, 189-192	0.4	2
44	CVD Growth of 3C-SiC on 4H-SiC Substrate. <i>Materials Science Forum</i> , 2012 , 711, 16-21	0.4	2
43	Influence of Cooling Rate after High Temperature Annealing on Deep Levels in High-Purity Semi-Insulating 4H-SiC. <i>Materials Science Forum</i> , 2007 , 556-557, 371-374	0.4	2
42	Growth and Photoluminescence Study of Aluminium Doped SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2007 , 556-557, 97-100	0.4	2
41	Thick Epilayer for Power Devices. <i>Materials Science Forum</i> , 2007 , 556-557, 47-52	0.4	2
40	Correlation between Electrical and Optical Mapping of Boron Related Complexes in 4H-SiC. <i>Materials Science Forum</i> , 2003 , 433-436, 423-426	0.4	2
39	Doping-Related Strain in n-Doped 4H-SiC Crystals. <i>Materials Science Forum</i> , 2003 , 433-436, 269-272	0.4	2
38	Growth of Homoepitaxial Films on 4H-SiC(11-20) and 8° Off-Axis 4H-SiC(0001) Substrates and their Characterization. <i>Materials Science Forum</i> , 2004 , 457-460, 221-224	0.4	2
37	Enlarging the Usable Growth Area in a Hot-Wall Silicon Carbide CVD Reactor by Using Simulation. <i>Materials Science Forum</i> , 2001 , 353-356, 99-102	0.4	2
36	Influence of Epitaxial Layer on SiC Schottky Diode Gas Sensors Operated under High-Temperature Conditions. <i>Materials Science Forum</i> , 2002 , 389-393, 1423-1426	0.4	2
35	Electrical Characterization of High-Voltage 4H-SiC Diodes on High-Temperature CVD-Grown Epitaxial Layers. <i>Materials Science Forum</i> , 2002 , 389-393, 1285-1288	0.4	2

34	Near Band-Gap Emission in V-Implanted and Annealed 4H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 497-500	0.4	2
33	Important Nonradiative Grown-In Defects in MBE-Grown Si and SiGe/Si Heterostructures. <i>Materials Science Forum</i> , 1995 , 196-201, 473-478	0.4	2
32	Structural Investigation of Heteroepitaxial 3C-SiC Grown on 4H-SiC Substrates. <i>Materials Science Forum</i> , 2013 , 740-742, 319-322	0.4	1
31	Optical Properties of the Niobium Centre in 4H, 6H, and 15R SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 405-408	0.4	1
30	Photoluminescence of 8H-SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 347-350	0.4	1
29	Optical and Structural Properties of In-Grown Stacking Faults in 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2010 , 645-648, 307-310	0.4	1
28	Effect of Inter-Well Coupling between 3C and 6H in-Grown Stacking Faults in 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2011 , 679-680, 314-317	0.4	1
27	Electrical and Optical Properties of High-Purity Epilayers Grown by the Low-Temperature Chloro-Carbon Growth Method. <i>Materials Science Forum</i> , 2012 , 717-720, 129-132	0.4	1
26	Low Temperature Photoluminescence Investigation of 3-Inch SiC Wafers for Power Device Applications. <i>Materials Science Forum</i> , 2012 , 711, 164-168	0.4	1
25	Titanium Related Luminescence in SiC. <i>Materials Science Forum</i> , 2008 , 600-603, 461-464	0.4	1
24	Improved SiC Epitaxial Material for Bipolar Applications. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1069, 1		1
23	Wave-Function Symmetry and the Properties of Shallow P Donors in 4H SiC. <i>Materials Science Forum</i> , 2008 , 600-603, 445-448	0.4	1
22	Shallow P Donors in 3C-, 4H- and 6H-SiC. <i>Materials Science Forum</i> , 2006 , 527-529, 593-596	0.4	1
21	Photoluminescence of Phosphorous Doped SiC. <i>Materials Science Forum</i> , 2006 , 527-529, 589-592	0.4	1
20	Epitaxial Growth of 4H-SiC in a Vertical Hot-Wall CVD Reactor: Comparison between Up- and Down-Flow Orientations. <i>Materials Science Forum</i> , 2001 , 353-356, 91-94	0.4	1
19	Bound Exciton Recombination in Electron Irradiated 4H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 477-480	0.4	1
18	The Electronic Structure of the UD-4 Defect in 4H, 6H and 15R SiC. <i>Materials Science Forum</i> , 2008 , 600-603, 397-400	0.4	0
17	Investigation of the Electronic Structure of the UD-4 Defect in 4H-SiC by Optical Techniques. <i>Materials Science Forum</i> , 2006 , 527-529, 461-464	0.4	0

16	Properties of the Bound Excitons Associated to the 3838Å Line in 4H-SiC and the 4182Å Line in 6H-SiC. <i>Materials Science Forum</i> , 2004 , 457-460, 549-554	0.4	0
15	Infrared Optical Properties of 3C, 4H and 6H Silicon Carbide. <i>Materials Science Forum</i> , 2003 , 433-436, 329-332	0.4	0
14	Changes in the Exciton-Related Photoluminescence of 4H- and 6H-SiC Induced by Uniaxial Stress. <i>Materials Science Forum</i> , 1998 , 264-268, 489-492	0.4	0
13	Chemical Vapor Deposition of Boron Nitride Thin Films on SiC. <i>Materials Science Forum</i> , 2015 , 821-823, 990-994	0.4	
12	Characteristics of Low-Temperature Solution-Processed Boron Nitride Thin Films for Flexible Nanoelectronics. <i>Journal of Nanoscience and Nanotechnology</i> , 2017 , 17, 8567-8570	1.3	
11	Photoluminescence of 10H-SiC. <i>Materials Science Forum</i> , 2016 , 858, 269-273	0.4	
10	Comparative Study on Dry Etching of Band Edge SiC Nano-Pillars. <i>Materials Science Forum</i> , 2013 , 740-742, 817-820	0.4	
9	Growth of 4H-SiC Epitaxial Layers on 4° Off-Axis Si-Face Substrates. <i>Materials Science Forum</i> , 2009 , 615-617, 81-84	0.4	
8	Temperature Dependence and Selective Excitation of the Phosphorus Related Photoluminescence in 4H-SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 263-266	0.4	
7	Donor-Acceptor Pair Luminescence of P-Al and N-Al Pairs in 3C-SiC and the Ionization Energy of the P Donor. <i>Materials Science Forum</i> , 2011 , 679-680, 245-248	0.4	
6	Electronic Configuration of Tungsten in 4H-, 6H-, and 15R-SiC. <i>Materials Science Forum</i> , 2012 , 717-720, 211-216	0.4	
5	Donor-Acceptor Pair Luminescence of Phosphorus-Aluminum and Nitrogen-Aluminum Pairs in 4H SiC. <i>Materials Science Forum</i> , 2006 , 527-529, 601-604	0.4	
4	CVD of 6H-SiC on Non-Basal Quasi Polar Faces. <i>Materials Science Forum</i> , 2007 , 556-557, 73-76	0.4	
3	Optical Properties of Aluminium and Nitrogen in Compensated 4H-SiC Epitaxial Layers. <i>Materials Research Society Symposia Proceedings</i> , 2000 , 640, 1		
2	Ga Bound Excitons in 6H-SiC. <i>Materials Science Forum</i> , 1995 , 196-201, 91-96	0.4	
1	Defect Formation and Recombination Processes in p-Type Modulation-Doped Si Epilayers. <i>Materials Science Forum</i> , 1995 , 196-201, 479-484	0.4	